



August 2015

FSBB15CH60D

Motion SPM[®] 3 Series

Features

- UL Certified No. E209204 (UL1557)
- 600 V - 15 A 3-Phase IGBT Inverter with Integral Gate Drivers and Protection
- Low-Loss, Short-Circuit Rated IGBTs
- Very Low Thermal Resistance Using Al₂O₃ DBC Substrate
- Built-In Bootstrap Diodes and Dedicated Vs Pins Simplify PCB Layout
- Separate Open-Emitter Pins from Low-Side IGBTs for Three-Phase Current Sensing
- Single-Grounded Power Supply
- LVIC Temperature-Sensing Built-In for Temperature Monitoring
- Isolation Rating: 2500 V_{rms} / 1 min.

Applications

- Motion Control - Home Appliance / Industrial Motor

Related Resources

- [AN-9044 - Motion SPM[®] 3 Series Users Guide](#)

FSBB15CH60D is an advanced Motion SPM[®] 3 module providing a fully-featured, high-performance inverter output stage for AC Induction, BLDC, and PMSM motors. These modules integrate optimized gate drive of the built-in IGBTs to minimize EMI and losses, while also providing multiple on-module protection features including under-voltage lockouts, over-current shutdown, thermal monitoring of drive IC, and fault reporting. The built-in, high-speed HVIC requires only a single supply voltage and translates the incoming logic-level gate inputs to the high-voltage, high-current drive signals required to properly drive the module's internal IGBTs. Separate negative IGBT terminals are available for each phase to support the widest variety of control algorithms.

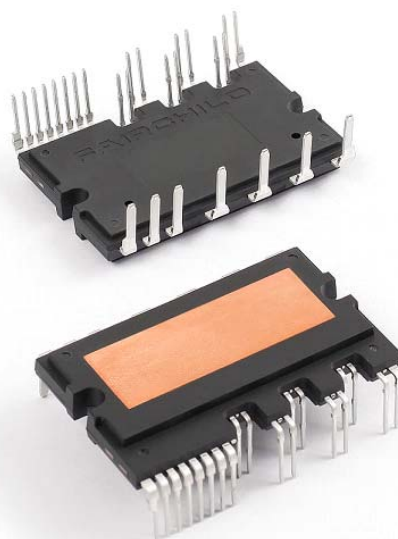


Figure 1. Package Overview

General Description

Package Marking and Ordering Information

Device	Device Marking	Package	Packing Type	Quantity
FSBB15CH60D	FSBB15CH60D	SPMCC-027	Rail	10

Integrated Power Functions

- 600 V - 15 A IGBT inverter for three-phase DC / AC power conversion (Please refer to Figure 3)

Integrated Drive, Protection and System Control Functions

- For inverter high-side IGBTs: gate drive circuit, high-voltage isolated high-speed level shifting control circuit Under-Voltage Lock-Out Protection (UVLO)
Note: Available bootstrap circuit example is given in Figures 5 and 14.
- For inverter low-side IGBTs: gate drive circuit, Short-Circuit Protection (SCP) control supply circuit Under-Voltage Lock-Out Protection (UVLO)
- Fault signaling: corresponding to UVLO (low-side supply) and SC faults
- Input interface: active-HIGH interface, works with 3.3 / 5 V logic, Schmitt-trigger input

Pin Configuration

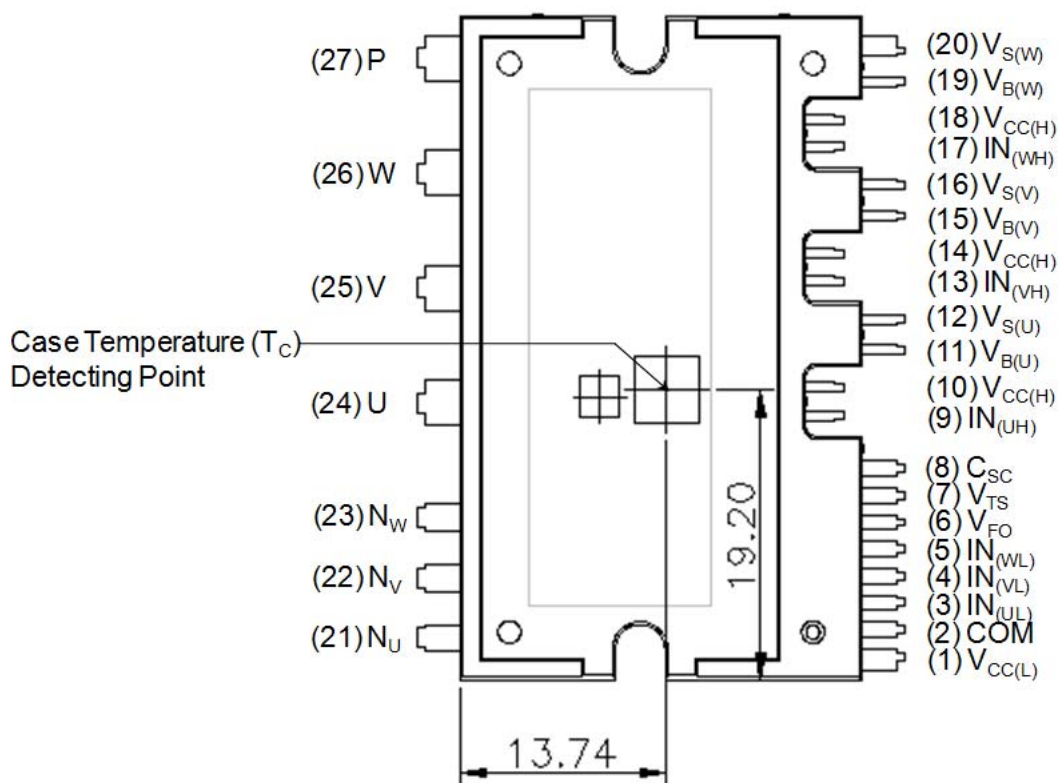


Figure 2. Top View

Pin Descriptions

Pin Number	Pin Name	Pin Description
1	$V_{CC(L)}$	Low-Side Common Bias Voltage for IC and IGBTs Driving
2	COM	Common Supply Ground
3	$IN_{(UL)}$	Signal Input for Low-Side U-Phase
4	$IN_{(VL)}$	Signal Input for Low-Side V-Phase
5	$IN_{(WL)}$	Signal Input for Low-Side W-Phase
6	V_{FO}	Fault Output
7	V_{TS}	Output for LVIC Temperature Sensing Voltage Output
8	C_{SC}	Capacitor (Low-Pass Filter) for Short-Circuit Current Detection Input
9	$IN_{(UH)}$	Signal Input for High-Side U-Phase
10	$V_{CC(H)}$	High-Side Common Bias Voltage for IC and IGBTs Driving
11	$V_{B(U)}$	High-Side Bias Voltage for U-Phase IGBT Driving
12	$V_{S(U)}$	High-Side Bias Voltage Ground for U-Phase IGBT Driving
13	$IN_{(VH)}$	Signal Input for High-Side V-Phase
14	$V_{CC(H)}$	High-Side Common Bias Voltage for IC and IGBTs Driving
15	$V_{B(V)}$	High-Side Bias Voltage for V-Phase IGBT Driving
16	$V_{S(V)}$	High-Side Bias Voltage Ground for V Phase IGBT Driving
17	$IN_{(WH)}$	Signal Input for High-Side W-Phase
18	$V_{CC(H)}$	High-Side Common Bias Voltage for IC and IGBTs Driving
19	$V_{B(W)}$	High-Side Bias Voltage for W-Phase IGBT Driving
20	$V_{S(W)}$	High-Side Bias Voltage Ground for W-Phase IGBT Driving
21	N_U	Negative DC-Link Input for U-Phase
22	N_V	Negative DC-Link Input for V-Phase
23	N_W	Negative DC-Link Input for W-Phase
24	U	Output for U-Phase
25	V	Output for V-Phase
26	W	Output for W-Phase
27	P	Positive DC-Link Input

Internal Equivalent Circuit and Input/Output Pins

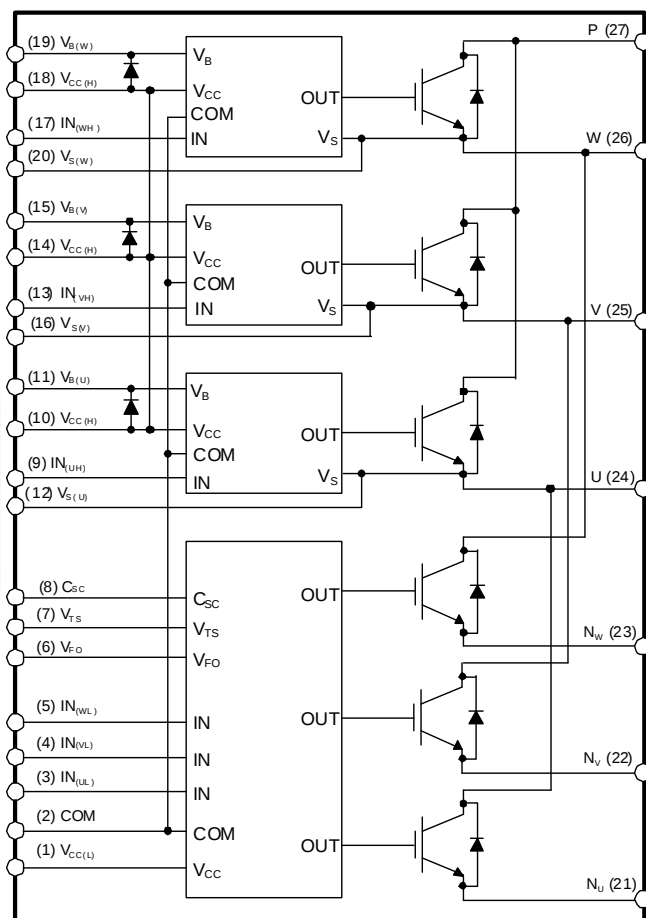


Figure 3. Internal Block Diagram

Notes:

1. Inverter low-side is composed of three IGBTs, freewheeling diodes for each IGBT, and one control IC. It has gate drive and protection functions.
2. Inverter power side is composed of four inverter DC-link input terminals and three inverter output terminals.
3. Inverter high-side is composed of three IGBTs, freewheeling diodes, and three drive ICs for each IGBT.

Absolute Maximum Ratings ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)**Inverter Part**

Symbol	Parameter	Conditions	Rating	Unit
V_{PN}	Supply Voltage	Applied between P - N_U , N_V , N_W	450	V
$V_{PN(\text{Surge})}$	Supply Voltage (Surge)	Applied between P - N_U , N_V , N_W	500	V
V_{CES}	Collector - Emitter Voltage		600	V
$\pm I_C$	Each IGBT Collector Current	$T_C = 25^\circ\text{C}$, $T_J \leq 150^\circ\text{C}$ (Note 4)	15	A
$\pm I_{CP}$	Each IGBT Collector Current (Peak)	$T_C = 25^\circ\text{C}$, $T_J \leq 150^\circ\text{C}$, Under 1 ms Pulse Width (Note 4)	30	A
P_C	Collector Dissipation	$T_C = 25^\circ\text{C}$ per One Chip (Note 4)	58	W
T_J	Operating Junction Temperature		-40 ~ 150	$^\circ\text{C}$

Control Part

Symbol	Parameter	Conditions	Rating	Unit
V_{CC}	Control Supply Voltage	Applied between $V_{CC(H)}$, $V_{CC(L)}$ - COM	20	V
V_{BS}	High-Side Control Bias Voltage	Applied between $V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$	20	V
V_{IN}	Input Signal Voltage	Applied between $IN_{(UH)}$, $IN_{(VH)}$, $IN_{(WH)}$, $IN_{(UL)}$, $IN_{(VL)}$, $IN_{(WL)}$ - COM	-0.3 ~ $V_{CC}+0.3$	V
V_{FO}	Fault Output Supply Voltage	Applied between V_{FO} - COM	-0.3 ~ $V_{CC}+0.3$	V
I_{FO}	Fault Output Current	Sink Current at V_{FO} pin	2	mA
V_{SC}	Current Sensing Input Voltage	Applied between C_{SC} - COM	-0.3 ~ $V_{CC}+0.3$	V

Bootstrap Diode Part

Symbol	Parameter	Conditions	Rating	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage		600	V
I_F	Forward Current	$T_C = 25^\circ\text{C}$, $T_J \leq 150^\circ\text{C}$ (Note 4)	0.5	A
I_{FP}	Forward Current (Peak)	$T_C = 25^\circ\text{C}$, $T_J \leq 150^\circ\text{C}$, Under 1 ms Pulse Width (Note 4)	2.0	A
T_J	Operating Junction Temperature		-40 ~ 150	$^\circ\text{C}$

Total System

Symbol	Parameter	Conditions	Rating	Unit
$V_{PN(\text{PROT})}$	Self Protection Supply Voltage Limit (Short Circuit Protection Capability)	$V_{CC} = V_{BS} = 13.5 \sim 16.5 \text{ V}$, $T_J = 150^\circ\text{C}$, Non-repetitive, < 2 μs	400	V
T_C	Module Case Operation Temperature	See Figure 2	-40 ~ 125	$^\circ\text{C}$
T_{STG}	Storage Temperature		-40 ~ 125	$^\circ\text{C}$
V_{ISO}	Isolation Voltage	60 Hz, Sinusoidal, AC 1 minute, Connection Pins to Heat Sink Plate	2500	V_{rms}

Thermal Resistance

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$R_{th(j-c)Q}$	Junction to Case Thermal Resistance (Note 5)	Inverter IGBT part (per 1 / 6 module)	-	-	2.15	$^\circ\text{C} / \text{W}$
$R_{th(j-c)F}$		Inverter FWD part (per 1 / 6 module)	-	-	2.85	$^\circ\text{C} / \text{W}$

Note:

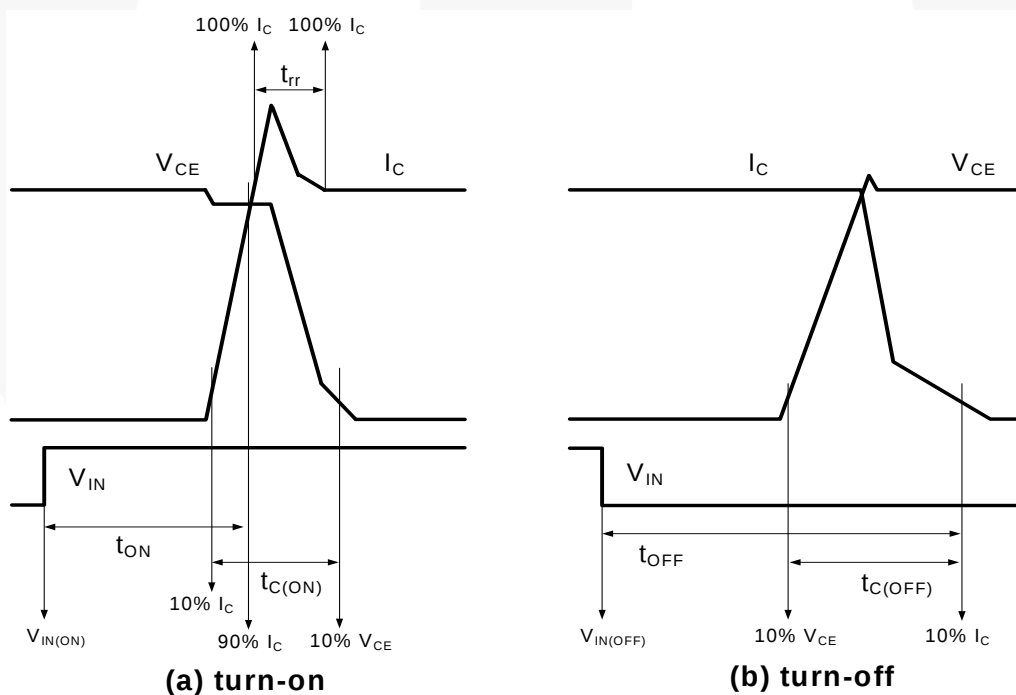
4. These values had been made an acquisition by the calculation considered to design factor.
 5. For the measurement point of case temperature (T_C), please refer to Figure 2.

Electrical Characteristics ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)**Inverter Part**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_{CE(SAT)}$	Collector - Emitter Saturation Voltage	$V_{CC} = V_{BS} = 15\text{ V}$ $V_{IN} = 5\text{ V}$ $I_C = 15\text{ A}$, $T_J = 25^\circ\text{C}$	-	-	2.0	V
V_F	FWDi Forward Voltage	$V_{IN} = 0\text{ V}$ $I_F = 15\text{ A}$, $T_J = 25^\circ\text{C}$	-	-	2.2	V
HS	t_{ON}	$V_{PN} = 300\text{ V}$, $V_{CC} = 15\text{ V}$, $I_C = 15\text{ A}$ $T_J = 25^\circ\text{C}$ $V_{IN} = 0\text{ V} \leftrightarrow 5\text{ V}$, Inductive Load See Figure 5 (Note 6)	-	1.0	-	μS
	$t_{C(ON)}$		-	0.4	-	μS
	t_{OFF}		-	0.4	-	μS
	$t_{C(OFF)}$		-	0.1	-	μS
	t_{rr}		-	0.1	-	μS
LS	t_{ON}	$V_{PN} = 300\text{ V}$, $V_{CC} = 15\text{ V}$, $I_C = 15\text{ A}$ $T_J = 25^\circ\text{C}$ $V_{IN} = 0\text{ V} \leftrightarrow 5\text{ V}$, Inductive Load See Figure 5 (Note 6)	-	0.8	-	μS
	$t_{C(ON)}$		-	0.3	-	μS
	t_{OFF}		-	0.8	-	μS
	$t_{C(OFF)}$		-	0.1	-	μS
	t_{rr}		-	0.1	-	μS
I_{CES}	Collector - Emitter Leakage Current	$V_{CE} = V_{CES}$	-	-	5	mA

Note:

6. t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. $t_{C(ON)}$ and $t_{C(OFF)}$ are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.

**Figure 4. Switching Time Definition**

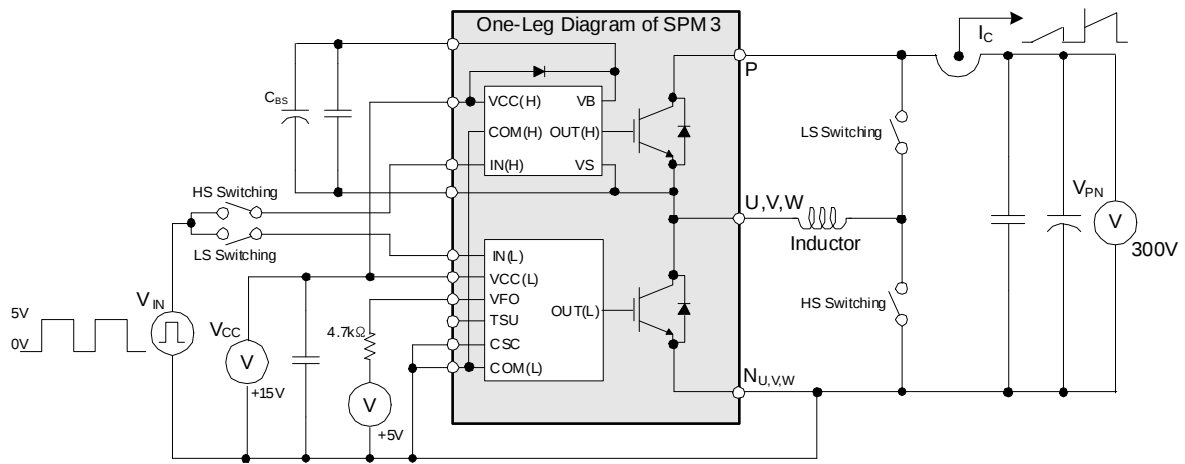


Figure 5. Example Circuit for Switching Test

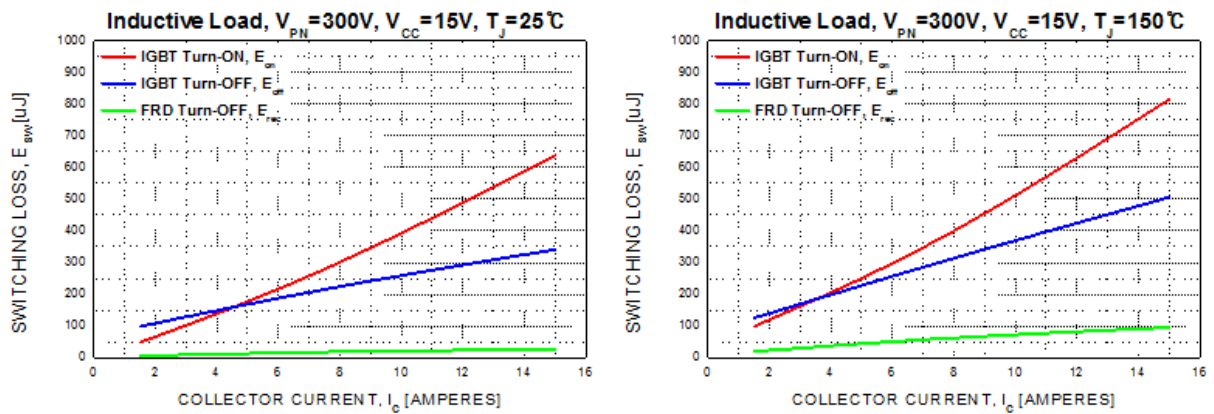


Figure 6. Switching Loss Characteristics

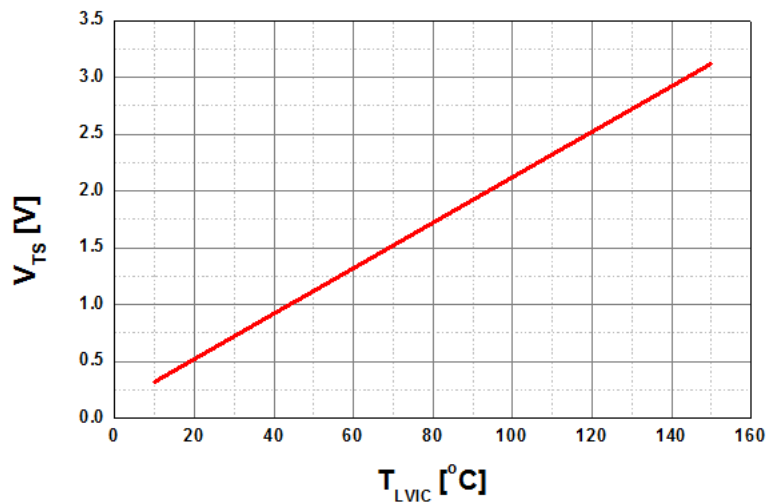


Figure 7. Temperature Profile of V_{TS} (Typical)

Bootstrap Diode Part

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage	$I_F = 0.1 \text{ A}$, $T_J = 25^\circ\text{C}$	-	2.5	-	V
t_{rr}	Reverse Recovery Time	$I_F = 0.1 \text{ A}$, $dI_F / dt = 50 \text{ A} / \mu\text{s}$, $T_J = 25^\circ\text{C}$	-	80	-	ns

Control Part

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Unit
I _{QCCH}	Quiescent V _{CC} Supply Current	V _{CC(H)} = 15 V, I _{N(UH,VH,WH)} = 0 V	V _{CC(H)} - COM	-	-	0.60	mA
I _{QCCL}		V _{CC(L)} = 15 V, I _{N(UL,VL,WL)} = 0 V	V _{CC(L)} - COM	-	-	6.0	mA
I _{PCCH}	Operating V _{CC} Supply Current	V _{CC(H)} = 15 V, f _{PWM} = 20 kHz, duty = 50%, applied to one PWM signal input for High-Side	V _{CC(H)} - COM	-	-	2.0	mA
I _{PCCL}		V _{CC(L)} = 15V, f _{PWM} = 20 kHz, duty = 50%, applied to one PWM signal input for Low-Side	V _{CC(L)} - COM	-	-	10.0	mA
I _{QBS}	Quiescent V _{BS} Supply Current	V _{BS} = 15 V, I _{N(UH, VH, WH)} = 0 V	V _{B(U)} - V _{S(U)} , V _{B(V)} - V _{S(V)} , V _{B(W)} - V _{S(W)}	-	-	0.50	mA
I _{PBS}	Operating V _{BS} Supply Current	V _{CC} = V _{BS} = 15 V, f _{PWM} = 20 kHz, duty = 50%, applied to one PWM signal input for High-Side	V _{B(U)} - V _{S(U)} , V _{B(V)} - V _{S(V)} , V _{B(W)} - V _{S(W)}	-	-	2.0	mA
V _{FOH}	Fault Output Voltage	V _{CC} = 15 V, V _{SC} = 0 V, V _{FO} Circuit: 4.7 kΩ to 5 V Pull-up		4.5	-	-	V
V _{FOL}		V _{CC} = 15 V, V _{SC} = 1 V, V _{FO} Circuit: 4.7 kΩ to 5 V Pull-up		-	-	0.5	V
V _{SC(ref)}	Short Circuit Trip Level	V _{CC} = 15 V (Note 7)	C _{SC} - COM _(L)	0.45	0.50	0.55	V
UV _{CCD}	Supply Circuit Under-Voltage Protection	Detection Level		9.8	-	13.3	V
UV _{CCR}		Reset Level		10.3	-	13.8	V
UV _{BSD}		Detection Level		10.0	-	12.0	V
UV _{BSR}		Reset Level		10.5	-	12.5	V
t _{FOD}	Fault-Out Pulse Width			50	-	-	μs
V _{TS}	LVIC Temperature Sensing Voltage Output	V _{CC(L)} = 15 V, T _{LVIC} = 25°C (Note 8) See Figure 7		540	640	740	mV
V _{IN(ON)}	ON Threshold Voltage	Applied between I _{N(UH, VH, WH)} - COM, I _{N(UL, VL, WL)} - COM		-	-	2.6	V
V _{IN(OFF)}	OFF Threshold Voltage			0.8	-	-	V

Note:

7. Short-circuit current protection is functioning only at the low-sides.

8. T_{LVIC} is the temperature of LVIC itself. V_{TS} is only for sensing temperature of LVIC and can not shutdown IGBTs automatically.

Recommended Operating Conditions

Symbol	Parameter	Conditions	Value			Unit
			Min.	Typ.	Max.	
V_{PN}	Supply Voltage	Applied between P - N_U , N_V , N_W	-	300	400	V
V_{CC}	Control Supply Voltage	Applied between $V_{CC(UH, VH, WH)}$ - COM, $V_{CC(L)}$ - COM	14.0	15	16.5	V
V_{BS}	High-Side Bias Voltage	Applied between $V_{B(U)} - V_{S(U)}$, $V_{B(V)} - V_{S(V)}$, $V_{B(W)} - V_{S(W)}$	13.0	15	18.5	V
dV_{CC} / dt , dV_{BS} / dt	Control Supply Variation		- 1	-	1	V / μ s
t_{dead}	Blanking Time for Preventing Arm - Short	For Each Input Signal	2.0	-	-	μ s
f_{PWM}	PWM Input Signal	$-40^{\circ}\text{C} \leq T_C \leq 125^{\circ}\text{C}$, $-40^{\circ}\text{C} \leq T_J \leq 150^{\circ}\text{C}$	-	-	20	kHz
V_{SEN}	Voltage for Current Sensing	Applied between N_U , N_V , N_W - COM (Including Surge Voltage)	- 4		4	V
T_J	Junction Temperature		- 40	-	150	$^{\circ}\text{C}$

Note:

9. This product might not make response if input pulse width is less than the recommended value.

Mechanical Characteristics and Ratings

Parameter	Conditions		Min.	Typ.	Max.	Unit
Mounting Torque	Mounting Screw: M3	Recommended 0.62 N•m	0.51	0.62	0.80	N•m
Device Flatness		See Figure 7	0	-	+150	μm
Weight			-	15.00	-	g

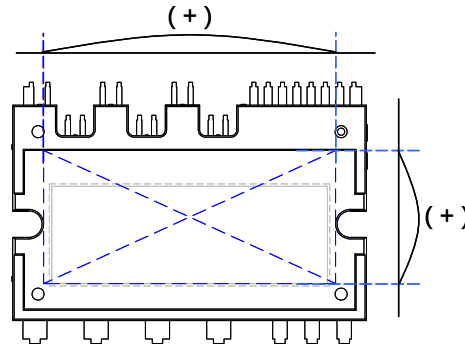


Figure 8. Flatness Measurement Position

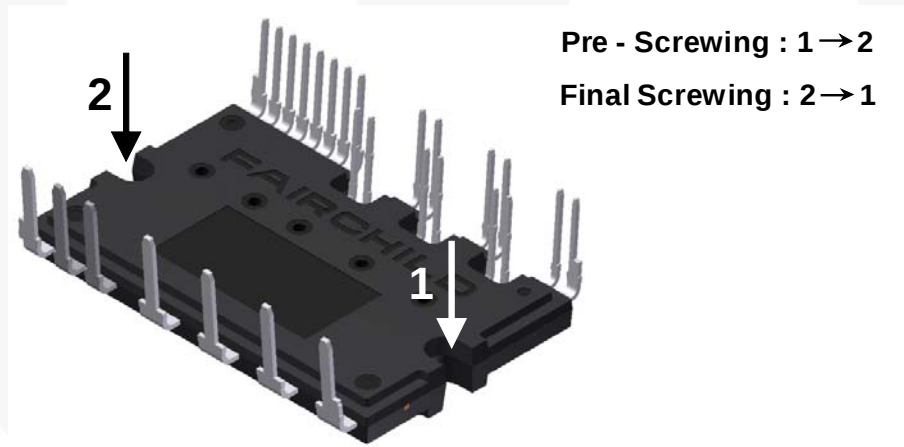


Figure 9. Mounting Screws Torque Order

Note:

10. Do not make over torque when mounting screws. Much mounting torque may cause DBC cracks, as well as bolts and Al heat-sink destruction.
11. Avoid one-sided tightening stress. Figure 9 shows the recommended torque order for mounting screws. Uneven mounting can cause the DBC substrate of package to be damaged. The pre-screwing torque is set to 20 ~ 30% of maximum torque rating.

Time Charts of SPMs Protective Function

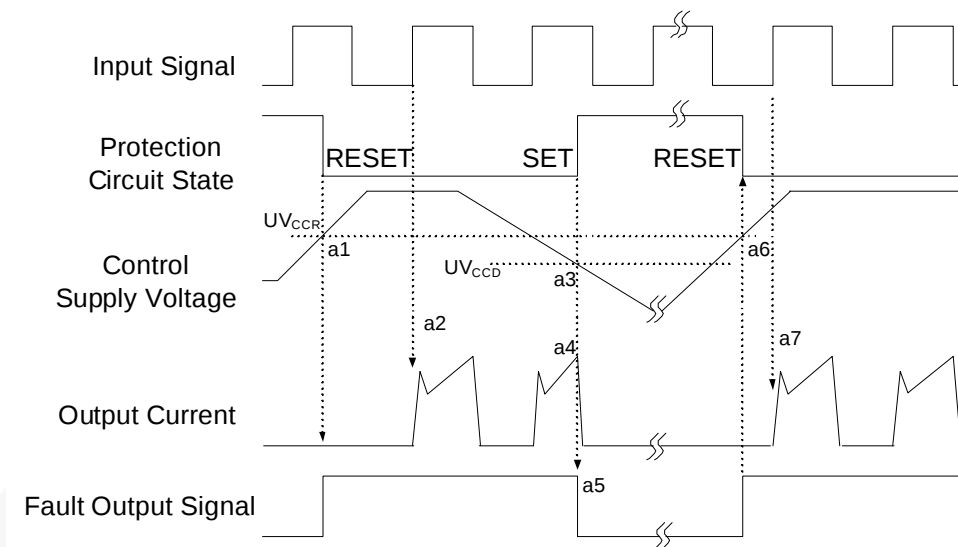


Figure 10. Under-Voltage Protection (Low-Side)

- a1 : Control supply voltage rises: After the voltage rises UV_{CCR} , the circuits start to operate when next input is applied.
- a2 : Normal operation: IGBT ON and carrying current.
- a3 : Under voltage detection (UV_{CCD}).
- a4 : IGBT OFF in spite of control input condition.
- a5 : Fault output operation starts with a fixed pulse width.
- a6 : Under voltage reset (UV_{CCR}).
- a7 : Normal operation: IGBT ON and carrying current by triggering next signal from LOW to HIGH.

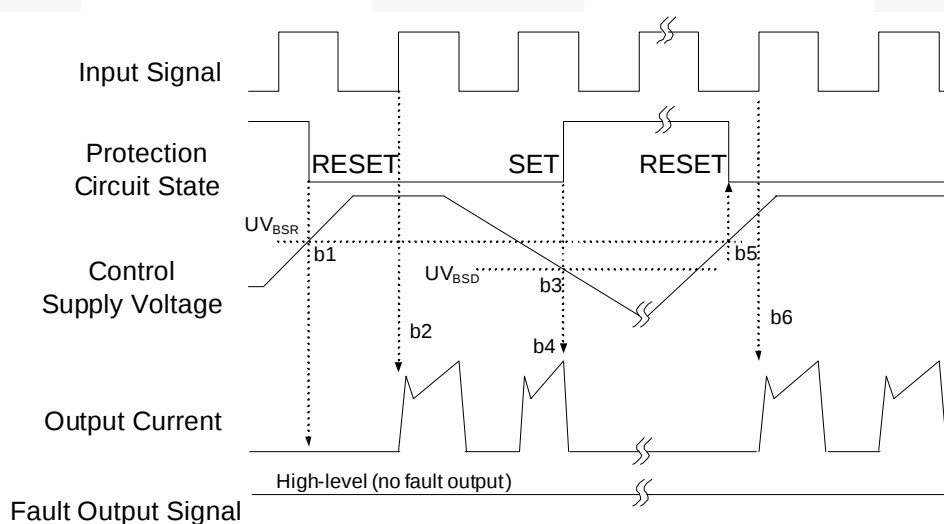


Figure 11. Under-Voltage Protection (High-Side)

- b1 : Control supply voltage rises: After the voltage reaches UV_{BSR} , the circuits start to operate when next input is applied.
- b2 : Normal operation: IGBT ON and carrying current.
- b3 : Under voltage detection (UV_{BSD}).
- b4 : IGBT OFF in spite of control input condition, but there is no fault output signal.
- b5 : Under voltage reset (UV_{BSR}).
- b6 : Normal operation: IGBT ON and carrying current by triggering next signal from LOW to HIGH.

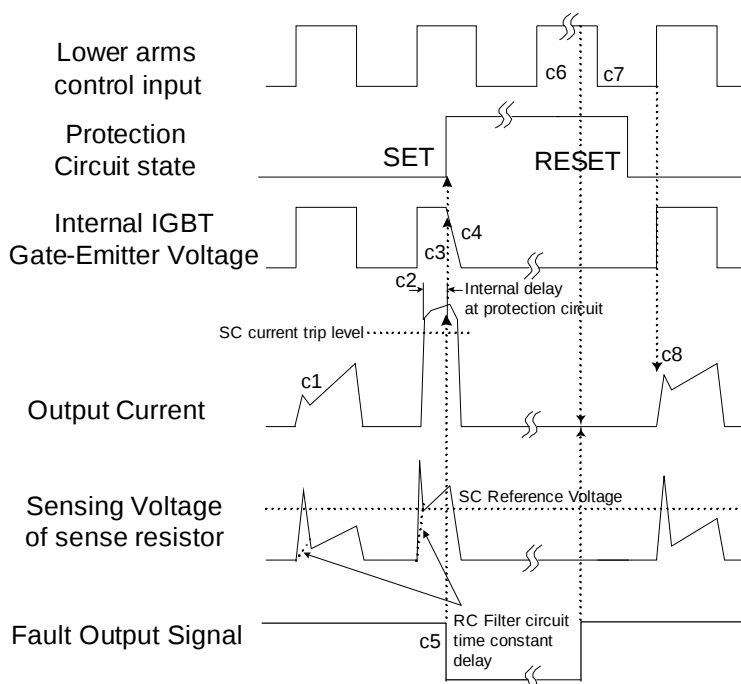


Figure 12. Short-Circuit Current Protection (Low-Side Operation only)

(with the external sense resistance and RC filter connection)

- c1 : Normal operation: IGBT ON and carrying current.
- c2 : Short circuit current detection (SC trigger).
- c3 : All low-side IGBT's gate are hard interrupted.
- c4 : All low-side IGBTs turn OFF.
- c5 : Fault output operation starts with a fixed pulse width.
- c6 : Input HIGH: IGBT ON state, but during the active period of fault output the IGBT doesn't turn ON.
- c7 : Fault output operation finishes, but IGBT doesn't turn on until triggering next signal from LOW to HIGH.
- c8 : Normal operation: IGBT ON and carrying current.

Input/Output Interface Circuit

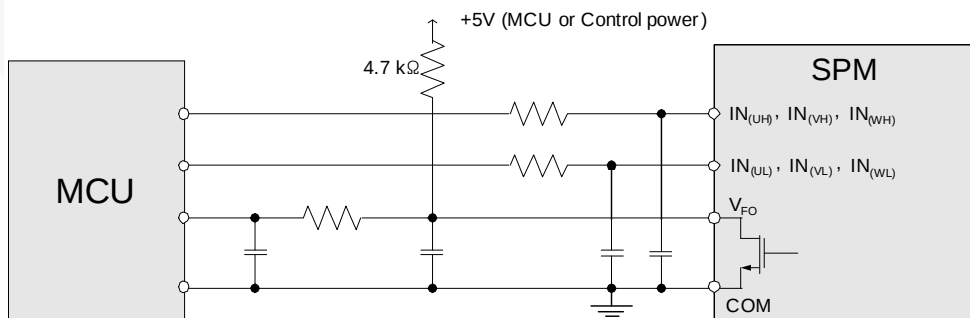


Figure 13. Recommended CPU I/O Interface Circuit

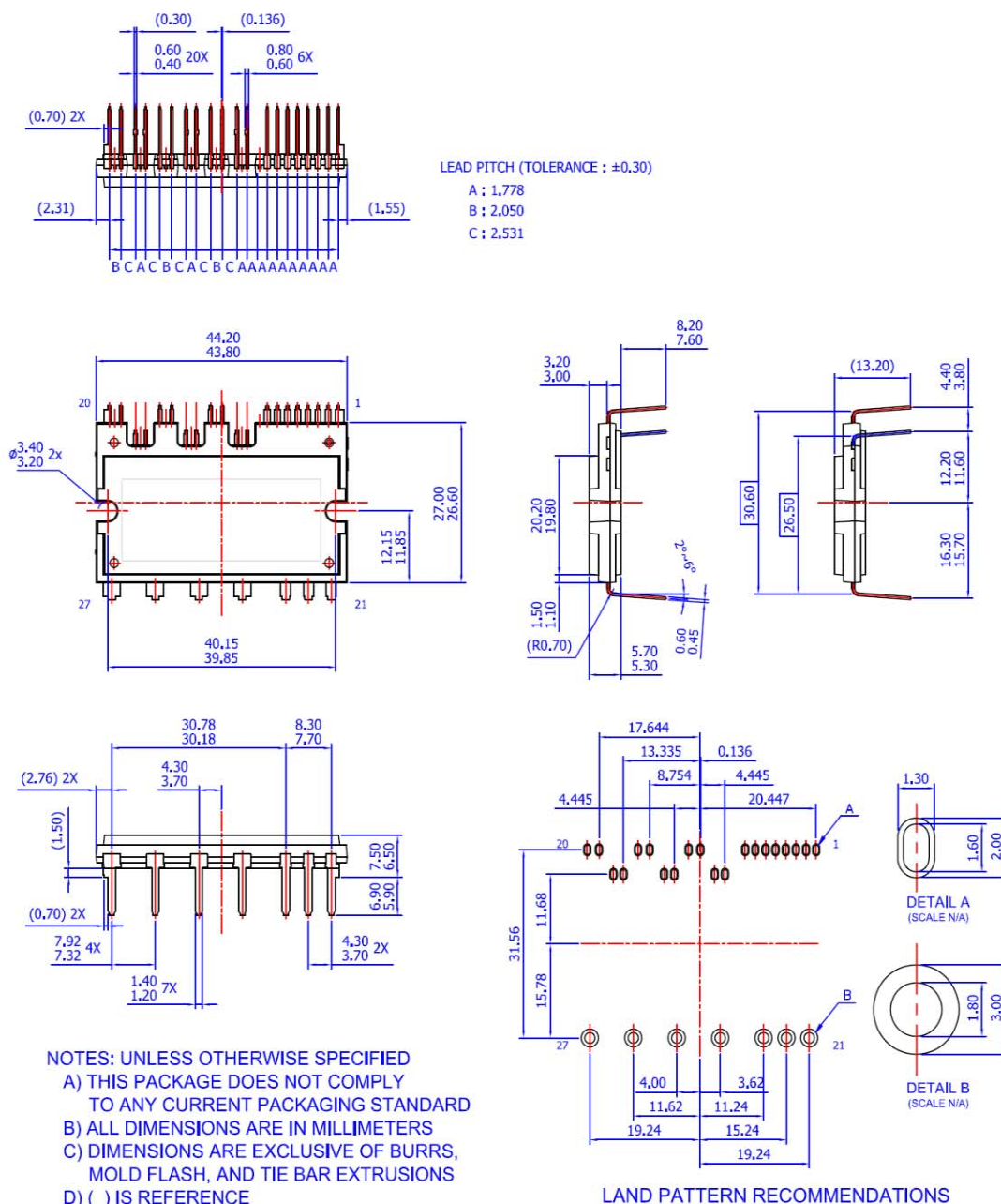
Note:

12. RC coupling at each input might change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board. The input signal section of the Motion SPM 3 product integrates 5 kΩ (typ.) pull-down resistor. Therefore, when using an external filtering resistor, please pay attention to the signal voltage drop at input terminal.

Note:

- www.fairchildsemi.com

Detailed Package Outline Drawings (FSBB15CH60D)



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ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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